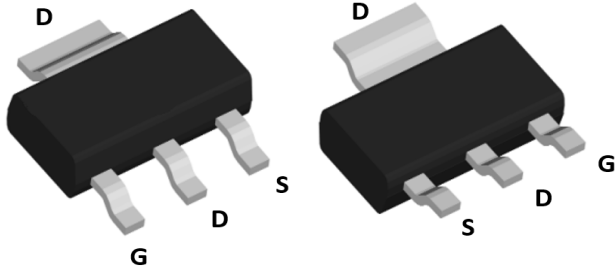
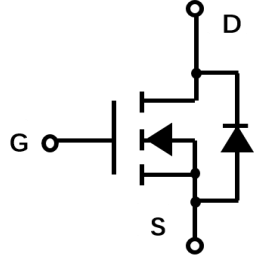


N-Channel Enhancement Mode Field Effect Transistor



SOT-223



Product Summary

- V_{DS} 100V
- I_D 4A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) < 110 mohm
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) < 120 mohm

General Description

- Trench Power MV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

- DC-DC Converters
- Power management functions

■ Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	100	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^\circ C$	4
		$T_A=70^\circ C$	3.2
Pulsed Drain Current ^A	I_{DM}	16	A
Total Power Dissipation @ $T_A=25^\circ C$	P_D	2.5	W
Thermal Resistance Junction-to-Ambient ^B	$R_{\theta JA}$	50	$^\circ C/W$
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	16	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJM04N10A	F2	1004	2500	/	40000	7" reel



YJM04N10A

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1	1.8	3.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=4A$		95	110	m Ω
		$V_{GS}=4.5V, I_D=3.2A$		100	120	
Diode Forward Voltage	V_{SD}	$I_S=4A, V_{GS}=0V$		0.8	1.2	V
Maximum Body-Diode Continuous Current	I_S				4	A
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1\text{MHz}$		800		pF
Output Capacitance	C_{oss}			40		
Reverse Transfer Capacitance	C_{rss}			32		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=50V, I_D=4A$		16		nC
Gate-Source Charge	Q_{gs}			2.5		
Gate-Drain Charge	Q_{gd}			2.6		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=50V, R_L=6.4\Omega$ $R_{GEN}=3\Omega$		6		ns
Turn-on Rise Time	t_r			41		
Turn-off Delay Time	$t_{D(off)}$			25		
Turn-off fall Time	t_f			8		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in 2 pad of 2oz copper.



YJM04N10A

■ Typical Performance Characteristics

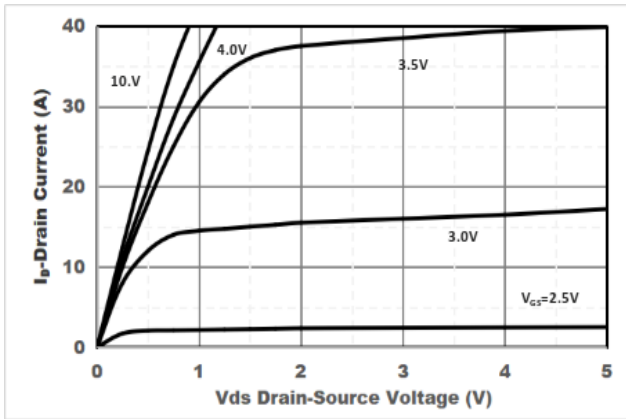


Figure1. Output Characteristics

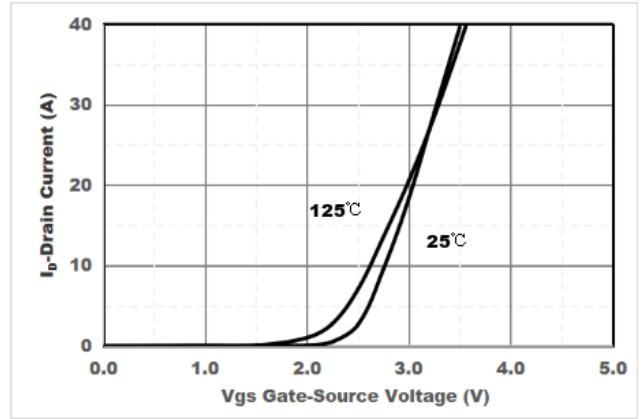


Figure2. Transfer Characteristics

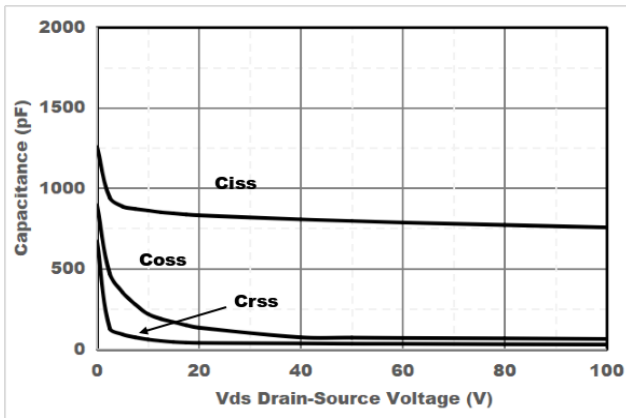


Figure3. Capacitance Characteristics

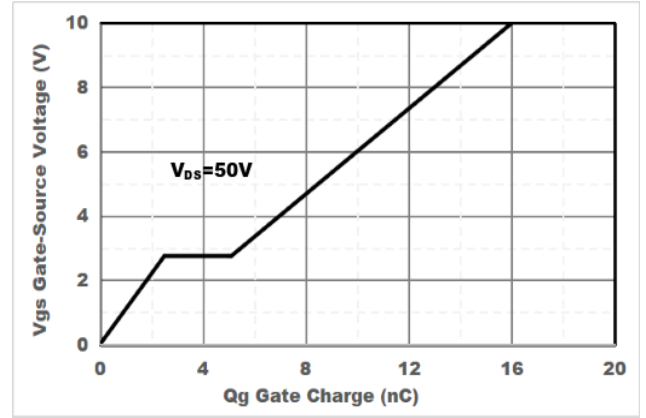


Figure4. Gate Charge

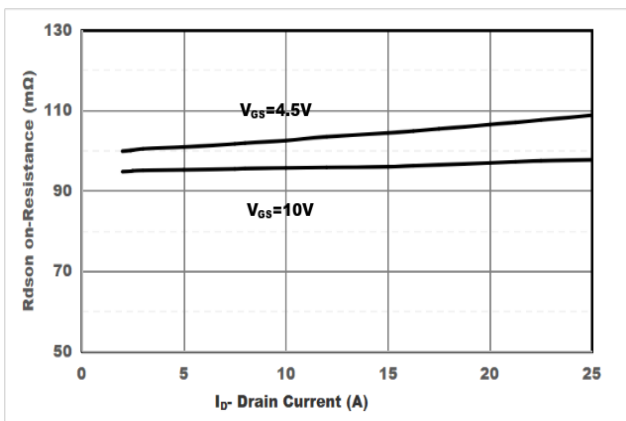


Figure5. Drain-Source on Resistance

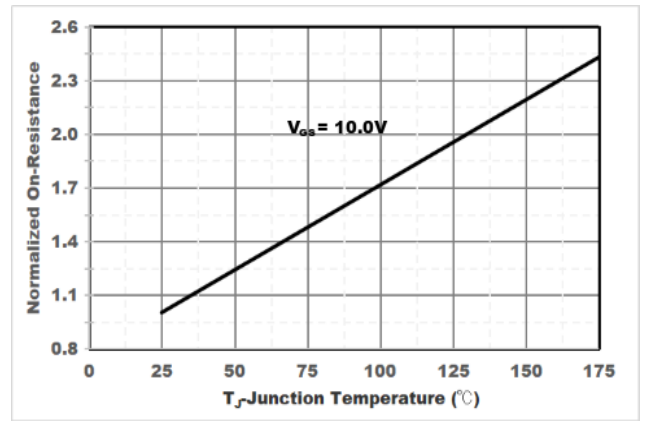


Figure6. Drain-Source on Resistance

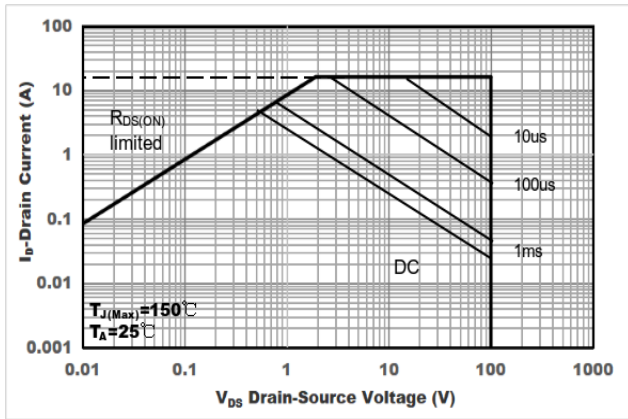


Figure7. Safe Operation Area

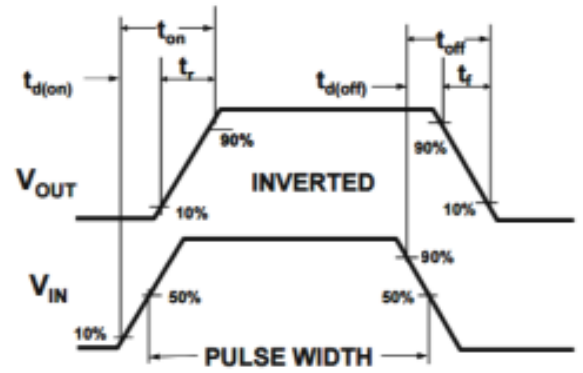
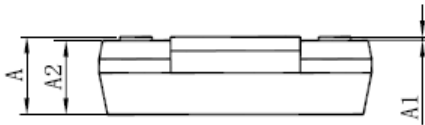
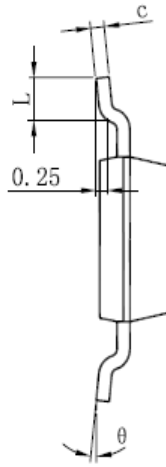
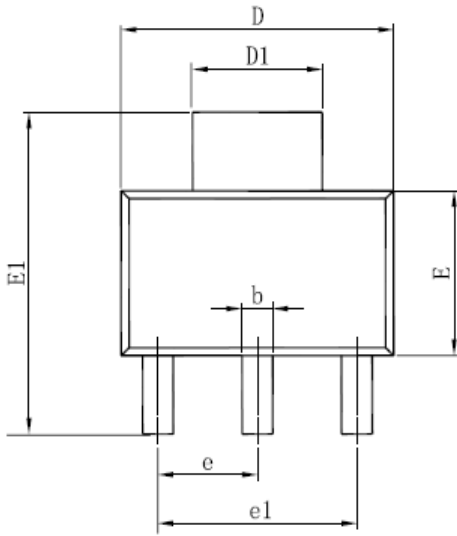


Figure8. Switching wave

■ SOT-223 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300(BSC)		0.091(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°



YJM04N10A

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